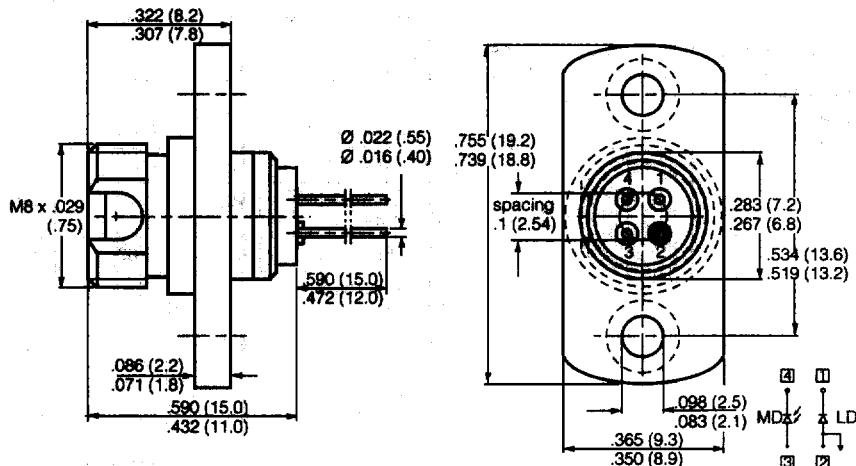


SIEMENS

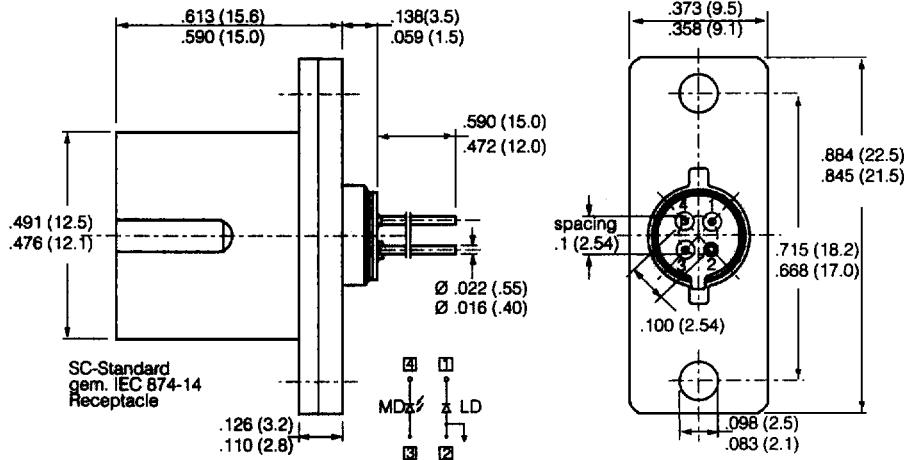
LOW POWER STL81007G/N 1500 nm Laser in Receptacle Package

Dimensions in inches (mm)

STL81007G



STL81007N



Fiber Optic
Components
Laser Diodes

FEATURES

- Designed for fiber optic networks
- Laser diode with multi-quantum well structure
- Suitable for bit rates up to 1 Gbit/s
- Ternary photodiode at rear mirror to monitor and control radiant power
- Hermetically sealed subcomponents, similar to TO-18
- SM receptacle with 2-hole flange and optional connector

Maximum Ratings Output power ratings refer to the SM fiber output. The operating temperature of the submount is identical to the case temperature.

Module

Operating and Storage Temperature Range
at Case(T_C , T_{STG}) -40 to +85°C
Soldering Temperature (T_S) 260°C
 $t_{max}=10$ s, 2 mm from bottom edge of case

Laser Diode

Direct Forward Current (I_{Fmax}) 120 mA
Radiant Power CW (Φ_e) 1 mW
Reverse Voltage (V_{Rmax}) 2 V

Monitor Diode

Reverse Voltage (V_{Rmax}) 10 V

Characteristics

All optical data refer to a coupled 10/125 μm SM fiber, $T_C=25^\circ\text{C}$

Parameter	Symbol	Value	Unit	
Laser Diode				
Optical Output Power CW	Φ_e	>0.2	mW	
Emission Wavelength, Center of Range	λ	1510–1590	nm	$\Phi_e=0.2\text{ mW}$
Spectral Bandwidth	$\Delta\lambda$	<5		$\Phi_e=0.2\text{ mW}$ (RMS)
Threshold Current	I_{th}	8–60	mA	-40 to +85°C
Forward Voltage	V_F	<1.5	V	$\Phi_e=0.2\text{ mW}$
Radiant Power at Threshold	Φ_{eth}	<10	μW	
Slope Efficiency	η	8–60	mW/A	-40 to +85°C
Differential Series Resistance	r_S	<8	W	
Rise Time/Fall Time	t_R, t_F	<1	ns	
Monitor Diode				
Dark Current	I_R	<500	nA	$V_R=5\text{ V}, \Phi_e=0,$ $T_C=85^\circ\text{C}$
Photocurrent	I_P	100–1000	μA	$\Phi_e=0.2\text{ mW}$